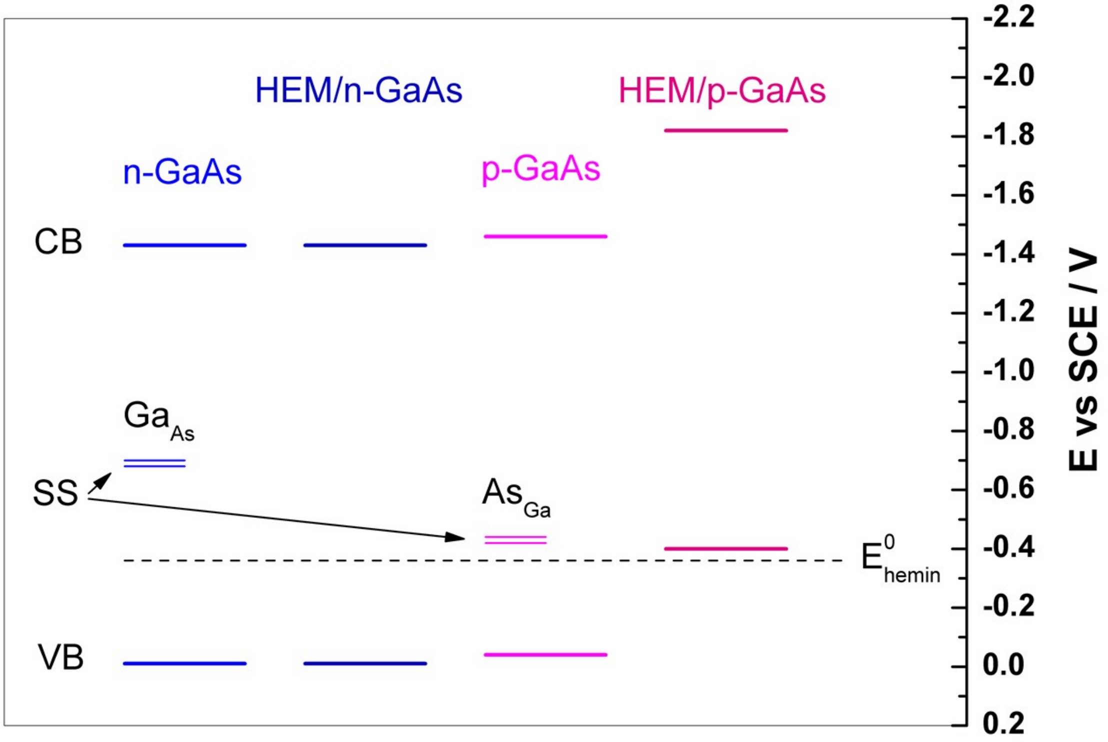
Electronic Supplementary Material (ESI) for RSC Advances.



Energy bands diagram showing the relative position on the electrochemical scale of the conduction (CB) and the valence (VB) band-edges for the bare and the hemin-covered n- and p-GaAs(100) with respect to the formal potential, E^0, of the hemin redox process in PBS solution. The positions of the main groups of surface states (SS), Ga_{As} and As_{Ga}, in the semiconductor bandgap are also shown.